

N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A)
150	98 at V _{GS} = 10 V	30
	110 at V _{GS} = 4.5 V	

FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g and UIS tested

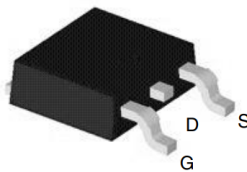


RoHS
COMPLIANT

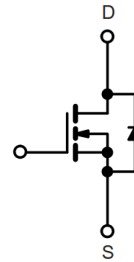
APPLICATIONS

- Primary Side Switch

TO-252 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C) ^b	I _D	T _C = 25 °C	30
		T _C = 125 °C	19
Pulsed Drain Current	I _{DM}	90	A
Continuous Source Current (Diode Conduction)	I _S	30	
Avalanche Current	I _{AR}	25	
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH E _{AR}	70	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	93 ^b
		T _A = 25 °C	2.9 ^a
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	16	20	°C/W
		Steady State	45	55	
Junction-to-Case	R _{thJC}	2	2.4		

Notes:

- Surface mounted on 1" x 1" FR4 board.
- See SOA curve for voltage derating.

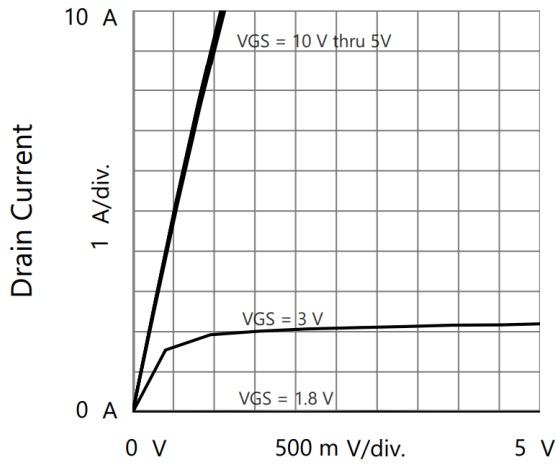
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		98	115	m Ω
		$V_{GS} = 10\text{ V}, I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$		105	123	
		$V_{GS} = 10\text{ V}, I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$		120	145	
		$V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$		110	132	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 10\text{ A}$		25		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 75\text{ V}, f = 1\text{ MHz}$		955		pF
Output Capacitance	C_{oss}			41		
Reverse Transfer Capacitance	C_{rss}			30		
Total Gate Charge ^c	Q_g	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		26		nC
Gate-Source Charge ^c	Q_{gs}			2		
Gate-Drain Charge ^c	Q_{gd}			19		
Gate Resistance	R_g	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		9		Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		8		ns
Rise Time ^c	t_r			35		
Turn-Off Delay Time ^c	$t_{d(off)}$			17		
Fall Time ^c	t_f			30		
Source-Drain Diode Ratings and Characteristic ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				90	A
Diode Forward Voltage ^b	V_{SD}	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		55		ns

Notes:

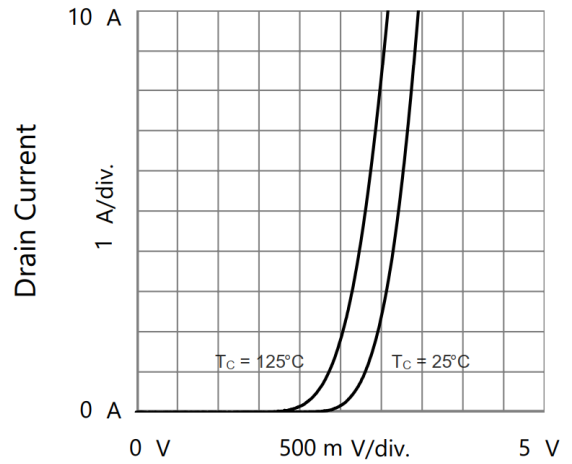
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

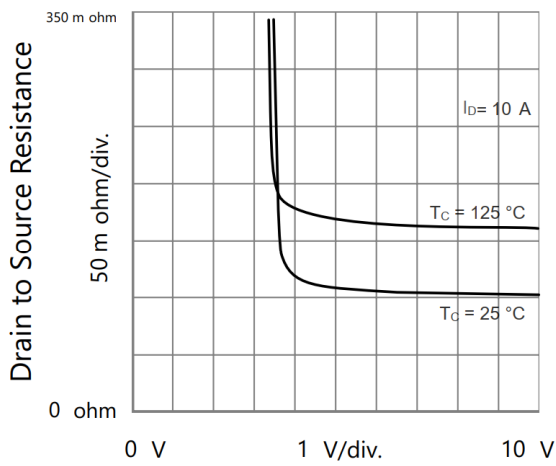
TYPICAL CHARACTERISTICS (25 °C unless noted)



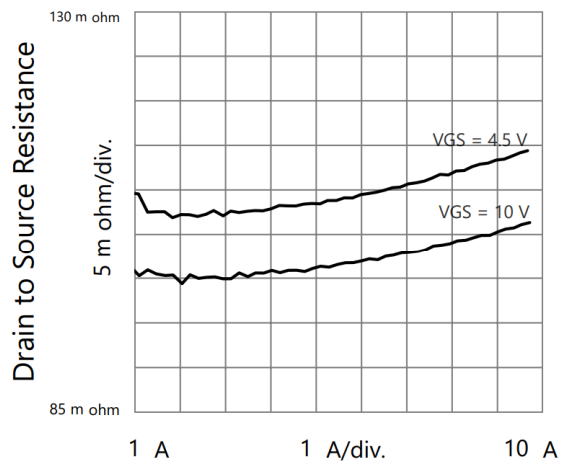
Drain to Source Voltage
Output Characteristics



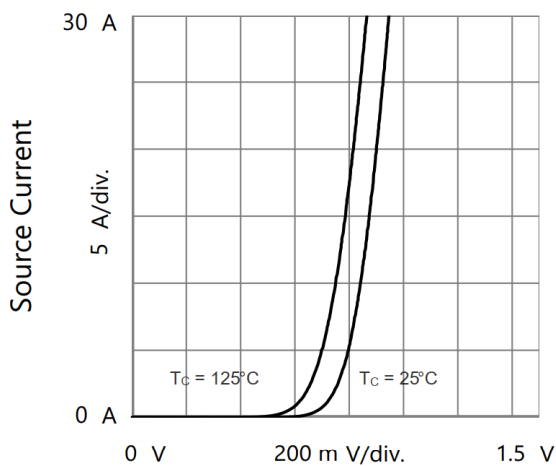
Gate to Source Voltage
Transfer Characteristics



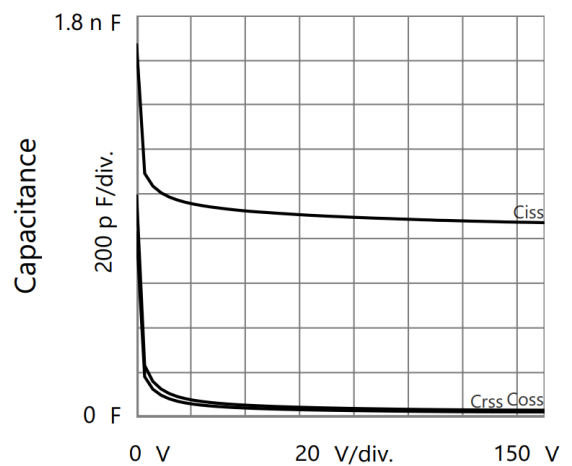
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

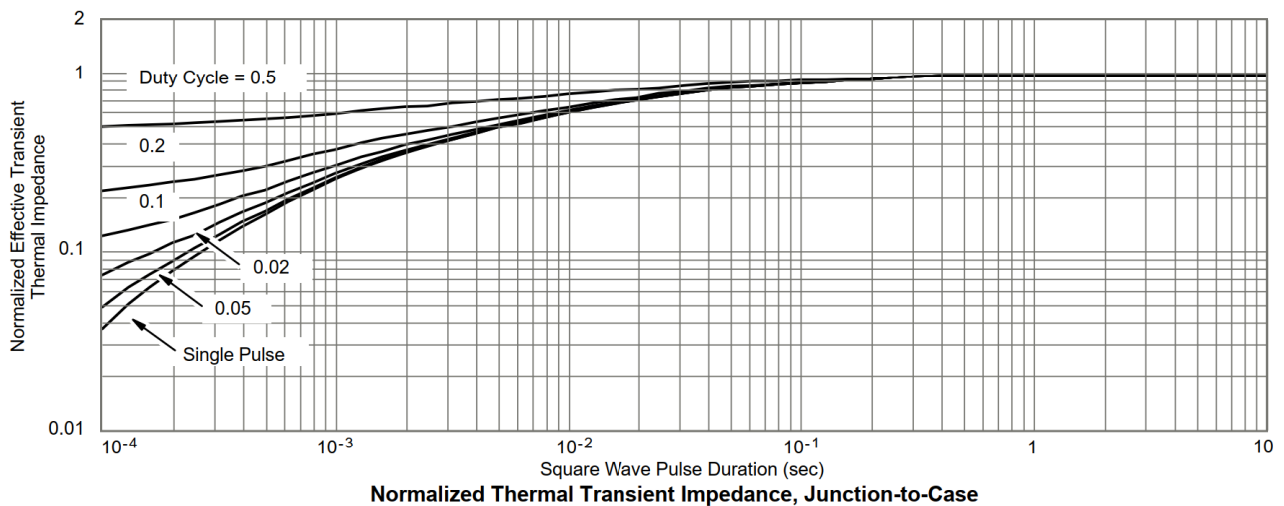
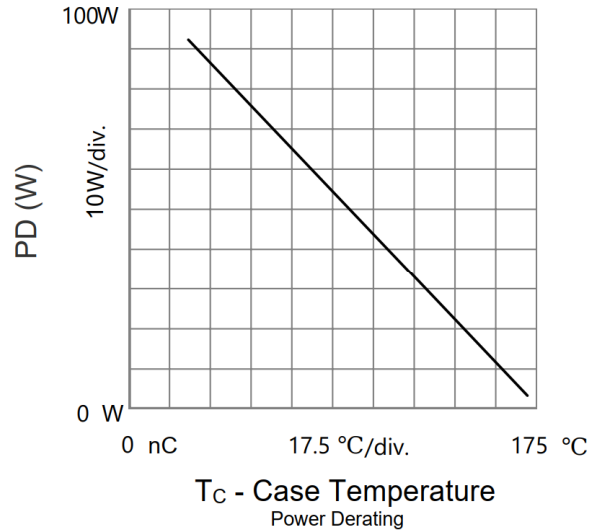
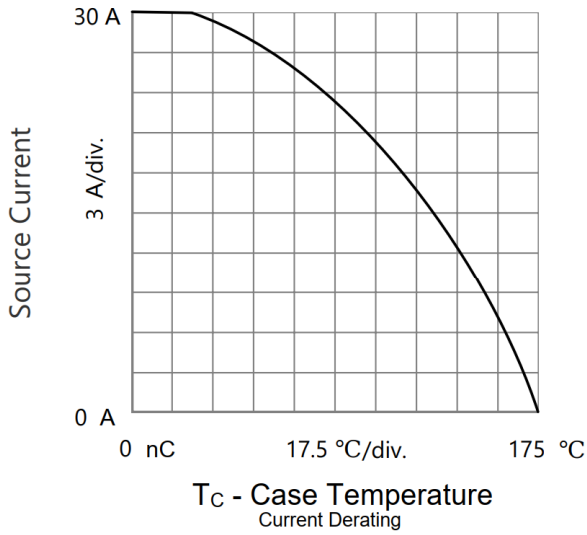
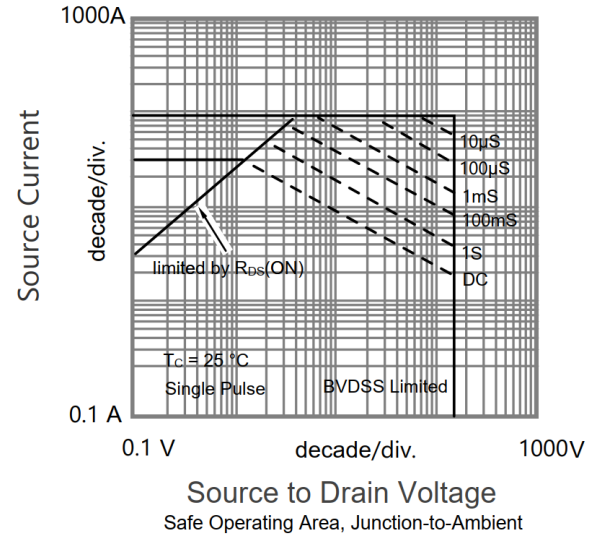
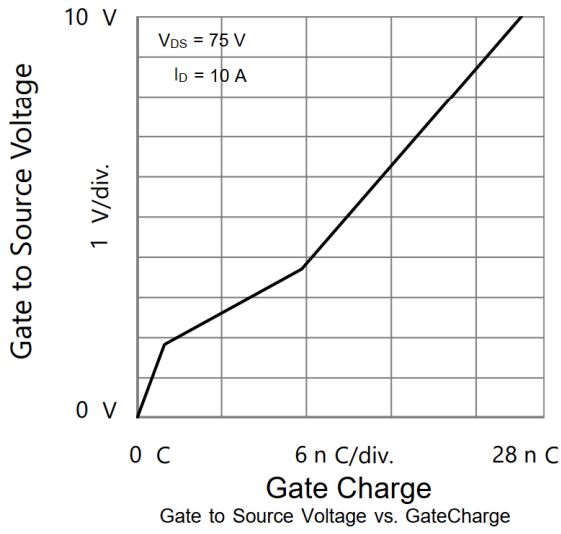


Source to Drain Voltage
Body Diode Forward Characteristics

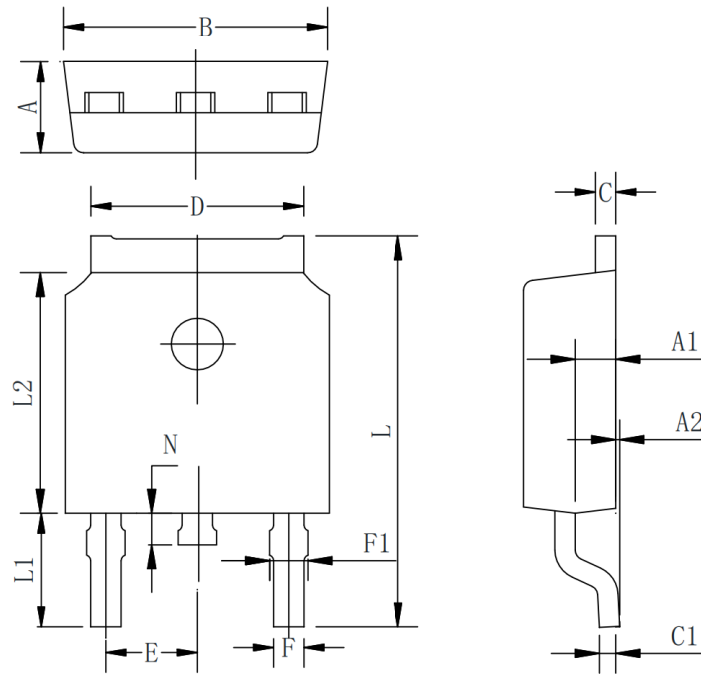


Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS (25 °C unless noted)



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Typ	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
B	6.40	6.60	6.80
C	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
E	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05

v

°C

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